



## **IRF840BPBF Information**



For Reference Only

**Part Number** IRF840BPBF **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 8.7A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **IRF840BPBF Specifications**

Manufacturer Part Number  Manufacturer  Vishay Siliconix  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-220-3  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Brive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Refor (Tell  Mosfet (Tell  Supplier Device Package  TO-220AB  Package / Case  TO-220-3  Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Tourent - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature Power Dissipation (Max) Rds On (Max) Rds On (Max) Rds On (Max) Rds On (Max) Respectively Rds On (Max) @ Id, Vgs Rds O	Manufacturer Part Number	IRF840BPBF
Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         8.7A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         30nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         527pF @ 100V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         156W (Tc)           Rds On (Max) @ Id, Vgs         850 mOhm @ 4A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3	Manufacturer	Vishay Siliconix
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Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

#### **IRF840BPBF** Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRF840BPBF Payment Methods**



















### **IRF840BPBF Shipping Methods**













If you have any question about IRF840BPBF, please do not hesitate to contact us!

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